

# Chen Pan

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/9150818/publications.pdf>

Version: 2024-02-01

22  
papers

2,375  
citations

516710

16  
h-index

642732

23  
g-index

24  
all docs

24  
docs citations

24  
times ranked

3781  
citing authors

| #  | ARTICLE   | IF   | CITATIONS |
|----|---|------|-----------|
| 1  | Nonvolatile van der Waals Heterostructure Phototransistor for Encrypted Optoelectronic Logic Circuit. ACS Nano, 2022, 16, 4528-4535.  | 14.6 | 34        |
| 2  | Networking retinomorphic sensor with memristive crossbar for brain-inspired visual perception. National Science Review, 2021, 8, nwaa172.   | 9.5  | 77        |
| 3  | Temperature-sensitive spatial distribution of defects in $\text{PdSe}_2$ flakes. Physical Review Materials, 2021, 5, .  | 26.0 | 191       |
| 4  | Scalable massively parallel computing using continuous-time data representation in nanoscale crossbar array. Nature Nanotechnology, 2021, 16, 1079-1085.  | 31.5 | 53        |
| 5  | A Braitenberg Vehicle Based on Memristive Neuromorphic Circuits. Advanced Intelligent Systems, 2020, 2, 1900103.  | 6.1  | 16        |
| 6  | Reconfigurable vertical field-effect transistor based on graphene/MoTe <sub>2</sub> /graphite heterostructure. Science China Information Sciences, 2020, 63, 1.                                       | 4.3  | 6         |
| 7  | Reconfigurable logic and neuromorphic circuits based on electrically tunable two-dimensional homojunctions. Nature Electronics, 2020, 3, 383-390.   | 26.0 | 191       |
| 8  | Gate-tunable van der Waals heterostructure for reconfigurable neural network vision sensor. Science Advances, 2020, 6, eaba6173.  | 10.3 | 202       |
| 9  | Chemical vapor deposition synthesis of two-dimensional freestanding transition metal oxychloride for electronic applications. Science China Information Sciences, 2019, 62, 1.                        | 4.3  | 5         |
| 10 | σ-Type Negative Differential Resistance in Semiconducting Transition-Metal Dichalcogenides. Advanced Electronic Materials, 2019, 5, 1800853.  | 5.1  | 17        |
| 11 | Vertical Transistors: Analog Circuit Applications Based on Ambipolar Graphene/MoTe <sub>2</sub> Vertical Transistors (Adv. Electron. Mater. 3/2018). Advanced Electronic Materials, 2018, 4, 1870015. | 5.1  | 0         |
| 12 | Robust memristors based on layered two-dimensional materials. Nature Electronics, 2018, 1, 130-136.   | 26.0 | 539       |
| 13 | Analog Circuit Applications Based on Ambipolar Graphene/MoTe <sub>2</sub> Vertical Transistors. Advanced Electronic Materials, 2018, 4, 1700662.  | 5.1  | 26        |
| 14 | Gate-Induced Interfacial Superconductivity in 1T-SnSe <sub>2</sub> . Nano Letters, 2018, 18, 1410-1415.   | 9.1  | 81        |
| 15 | Experimental Identification of Critical Condition for Drastically Enhancing Thermoelectric Power Factor of Two-Dimensional Layered Materials. Nano Letters, 2018, 18, 7538-7545.                      | 9.1  | 72        |
| 16 | Vertical WS <sub>2</sub> /SnS <sub>2</sub> van der Waals Heterostructure for Tunneling Transistors. Scientific Reports, 2018, 8, 17755.   | 3.3  | 40        |
| 17 | Gate-tunable weak antilocalization in a few-layer InSe. Physical Review B, 2018, 98, .  | 3.2  | 24        |
| 18 | Negative Photoconductance in van der Waals Heterostructure-Based Floating Gate Phototransistor. ACS Nano, 2018, 12, 9513-9520.  | 14.6 | 124       |

| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 19 | Gated tuned superconductivity and phonon softening in monolayer and bilayer MoS <sub>2</sub> . Npj Quantum Materials, 2017, 2, .   | 5.2  | 33        |
| 20 | Intrinsic p-type W-based transition metal dichalcogenide by substitutional Ta-doping. Applied Physics Letters, 2017, 111, .  | 3.3  | 26        |
| 21 | Van der Waals epitaxial growth and optoelectronics of large-scale WSe <sub>2</sub> /SnS <sub>2</sub> vertical bilayer p-n junctions. Nature Communications, 2017, 8, 1906. | 12.8 | 369       |
| 22 | Room temperature high-detectivity mid-infrared photodetectors based on black arsenic phosphorus. Science Advances, 2017, 3, e1700589.                                      | 10.3 | 419       |